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AMENDMENTS TO THE SPECIFICATION:

Please replace the paragraph starting at page 5, line 13 and ending at page 6, line 3 with

the following amended paragraph:

With reference to the accompanying drawings, FIG. 2 shows a cross-sectional view of an

alignment target 100 on a semiconductor device 102. Semiconductor device 102 may include a

first level of interconnect or wiring layer 104 in a dielectric layer 106. (Dielectric layers below

layer 106 have been removed for clarity.) Wiring layer 104 may contain a plurality of metal

fuses 108 and a metal wiring element(s) 110, which may be used to connect to subsequent wiring

layers or to the environment beyond the die. Other Another metal wiring clement(s) 112 may

also be provided that is part of another wiring layer or is a wire bond pad. Wiring layer 104 may

be constructed, for example, of copper. In normal circumstances, a number of dielectric layers

(not shown for clarity) will be provided above wiring layer 104. These dielectric layers may be

made of, for example, silicon nitride, oxide, nitride, etc.

Please replace the paragraph at page 6, lines 10-21 with the following amended

paragraph:

Alignment target 100 includes a surface 116 that is out of plane with and has substantially

the same first reflectivity as an adjacent surface (or field) 118. The first reflectivity may be

created by surface 116 being made of the same material as adjacent surface 118, or may be

created by residuals in dielectric layers over one or the other surface. A sidewall 120 of target

100 has a second reflectivity different than the first reflectivity. In one embodiment, the second

reflectivity is lower than the first reflectivity, but any reflectivity difference providing sufficient

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contrast between surfaces 116, 118 may be sufficient. In one embodiment, surface 116 is substantially planar. However, it is known to provide rough target surfaces. Sidewalls 120 may have a height greater than 500 Angstroms. In addition, as shown in FIG. 3, sidewalls 120 may form an angle α with a horizontal surface 116 of greater than 60 degrees. Surface 116 may be any desired shape, e.g., substantially orthogonal segments "L" or "T" shaped.

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